

D G Hasko

List of Publications by Year in descending order

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89
papers

6,188
citations

147801

31
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69250

77
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90
all docs

90
docs citations

90
times ranked

4249
citing authors

#	ARTICLE	IF	CITATIONS
1	Controllable interdot coupling in a Si-based double quantum dot system for a qubit gate. Journal of the Korean Physical Society, 2014, 64, 1626-1629.	0.7	0
2	Continuous weak measurement of a trapped electron using a percolation field effect transistor. Applied Physics Letters, 2013, 103, 093110.	3.3	3
3	Cryogenic single-shot spectroscopy of a floating poly-silicon gate transistor. Journal of Applied Physics, 2012, 112, 014510.	2.5	1
4	One electron-based smallest flexible logic cell. Applied Physics Letters, 2012, 101, .	3.3	18
5	Room-Temperature Charge Stability Modulated by Quantum Effects in a Nanoscale Silicon Island. Nano Letters, 2011, 11, 1591-1597.	9.1	74
6	Microwave-assisted transport via localized states in degenerately doped Si single electron transistors. Journal of Applied Physics, 2010, 108, 034509.	2.5	12
7	Si-based ultrasmall multiswitching single-electron transistor operating at room-temperature. Applied Physics Letters, 2010, 97, .	3.3	96
8	Microwave excitation of localized electrons in phosphorus-doped silicon single electron transistors. Journal of Applied Physics, 2009, 105, 104508.	2.5	5
9	Cryogenic instrumentation for fast current measurement in a silicon single electron transistor. Journal of Applied Physics, 2009, 106, 033705.	2.5	7
10	Trapped charge dynamics in a sol-gel based TiO ₂ high-k gate dielectric silicon metal-oxide-semiconductor field effect transistor. Journal of Physics Condensed Matter, 2009, 21, 215902.	1.8	16
11	Characterization of a sol-gel based high-k dielectric field effect transistor for cryogenic operation. Journal of Vacuum Science & Technology B, 2008, 26, 1887-1891.	1.3	10
12	Nanoelectromechanical switch with low voltage drive. Applied Physics Letters, 2008, 93, .	3.3	20
13	Single shot measurement of a silicon single electron transistor. Applied Physics Letters, 2008, 93, 192116.	3.3	10
14	Single shot measurement of the lifetime of a trapped electron in the gate dielectric of a high-k field effect transistor. Applied Physics Letters, 2008, 93, 193501.	3.3	4
15	Effect of sample temperature on the indentation-induced phase transitions in crystalline silicon. Journal of Applied Physics, 2007, 101, 083515.	2.5	24
16	Micro-SQUIDs with controllable asymmetry via hot-phonon controlled junctions. Physical Review B, 2007, 75, .	3.2	27
17	High performance ZnO nanowire field effect transistor using self-aligned nanogap gate electrodes. Applied Physics Letters, 2006, 89, 263102.	3.3	122
18	CNT based mechanical devices for ULSI memory. , 2006, , .		1

#	ARTICLE	IF	CITATIONS
19	Advantages of top-gate, high-k dielectric carbon nanotube field-effect transistors. Applied Physics Letters, 2006, 88, 113507.	3.3	83
20	Nanoscale capacitors based on metal-insulator-carbon nanotube-metal structures. Applied Physics Letters, 2005, 87, 263103.	3.3	32
21	Nanoelectromechanical switches with vertically aligned carbon nanotubes. Applied Physics Letters, 2005, 87, 163114.	3.3	153
22	Charge-Qubit Operation of an Isolated Double Quantum Dot. Physical Review Letters, 2005, 95, 090502.	7.8	336
23	Fabrication of a nanoelectromechanical switch using a suspended carbon nanotube. Applied Physics Letters, 2005, 86, 083105.	3.3	90
24	Carbon nanotube Schottky diode and directionally dependent field-effect transistor using asymmetrical contacts. Applied Physics Letters, 2005, 87, 253116.	3.3	160
25	Tungsten pedestal structure for nanotriode devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1298.	1.6	6
26	Controlled-junction superconducting quantum interference device via phonon injection. Applied Physics Letters, 2004, 84, 136-138.	3.3	4
27	Growth of high-quality single-wall carbon nanotubes without amorphous carbon formation. Applied Physics Letters, 2004, 84, 269-271.	3.3	79
28	Plasma enhanced chemical vapour deposition carbon nanotubes/nanofibres—how uniform do they grow?. Nanotechnology, 2003, 14, 204-211.	2.6	238
29	Nanoscale solid-state quantum computing. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2003, 361, 1473-1485.	3.4	52
30	Fabrication of self-aligned side gates to carbon nanotubes. Nanotechnology, 2003, 14, 290-293.	2.6	13
31	Suspended Multiwalled Carbon Nanotubes as Self-aligned Evaporation Masks. Journal of Nanoscience and Nanotechnology, 2003, 3, 325-328.	0.9	5
32	Hot phonon controlled-junction superconducting quantum interference device. Superconductor Science and Technology, 2003, 16, 1544-1549.	3.5	2
33	Field emission from dense, sparse, and patterned arrays of carbon nanofibers. Applied Physics Letters, 2002, 80, 2011-2013.	3.3	259
34	Uniform patterned growth of carbon nanotubes without surface carbon. Applied Physics Letters, 2001, 79, 1534-1536.	3.3	380
35	Fabrication of Microstructures for Microphotonic Circuit. Materials Research Society Symposia Proceedings, 2001, 694, 1.	0.1	0
36	Plasma Enhanced Chemical Vapour Deposited Carbon Nanotubes for Field Emission Applications. Materials Research Society Symposia Proceedings, 2001, 706, 1.	0.1	0

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37	Fabrication of Microstructures for Microphotonic Circuit. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	1
38	Nanolithography using ultrasonically assisted development of calixarene negative electron beam resist. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 311.	1.6	31
39	Fabrication of <5 nm width lines in poly(methylmethacrylate) resist using a water:isopropyl alcohol developer and ultrasonically-assisted development. Applied Physics Letters, 2001, 78, 2760-2762.	3.3	149
40	Thermally switched superconducting weak-link transistor with current gain. Applied Physics Letters, 2000, 76, 2295-2297.	3.3	10
41	Domain nucleation processes in mesoscopic Ni80Fe20 wire junctions. Journal of Applied Physics, 2000, 87, 3032-3036.	2.5	12
42	Influence of developer and development conditions on the behavior of high molecular weight electron beam resists. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 3441.	1.6	38
43	Characteristics of a free-standing superconducting nanobridge with an integrated heater fabricated using a self-aligned technique. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 3248.	1.6	5
44	Comparison of sensitivity and exposure latitude for polymethylmethacrylate, UVIII, and calixarene using conventional dip and ultrasonically assisted development. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 3390.	1.6	15
45	The "nanotriode": A nanoscale field-emission tube. Applied Physics Letters, 1999, 75, 2845-2847.	3.3	53
46	Magnetoresistance in modulated width Ni80Fe20 wires. Journal of Applied Physics, 1999, 85, 1689-1692.	2.5	10
47	Size-dependent spin-wave frequency in ferromagnetic wire-array structures. Physical Review B, 1998, 58, 345-350.	3.2	27
48	Fabrication and behavior of nanoscale field emission structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 2773.	1.6	11
49	Magnetostatic interactions and magnetization reversal in ferromagnetic wires. Physical Review B, 1997, 56, 3265-3270.	3.2	57
50	Magnetoresistance behavior of submicron Ni80Fe20 wires. Applied Physics Letters, 1997, 70, 1046-1048.	3.3	59
51	Nanoscale field emission structures for ultra-low voltage operation at atmospheric pressure. Applied Physics Letters, 1997, 71, 3159-3161.	3.3	50
52	Optimized process for the fabrication of mesoscopic magnetic structures. Journal of Applied Physics, 1997, 82, 469-473.	2.5	33
53	Detecting charge redistribution between edge states in a quantum dot. Journal of Physics Condensed Matter, 1994, 6, L273-L278.	1.8	4
54	Measurements of Coulomb blockade with a noninvasive voltage probe. Physical Review Letters, 1993, 70, 1311-1314.	7.8	535

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55	Thermopower of a one-dimensional ballistic constriction in the non-linear regime. Journal of Physics Condensed Matter, 1993, 5, 8055-8064.	1.8	22
56	Hopping conduction in a free-standing GaAs-AlGaAs heterostructure wire. Applied Physics Letters, 1993, 62, 2533-2535.	3.3	6
57	Lattice heating of free-standing ultra-fine GaAs wires by hot electrons. Semiconductor Science and Technology, 1992, 7, B231-B234.	2.0	17
58	The physics of the two-dimensional electron gas base vertical hot electron transistor. Semiconductor Science and Technology, 1992, 7, B536-B539.	2.0	3
59	Back-gated split-gate transistor: A one-dimensional ballistic channel with variable Fermi energy. Applied Physics Letters, 1992, 60, 2782-2784.	3.3	32
60	Two-dimensional electron-gas heating and phonon emission by hot ballistic electrons. Physical Review B, 1992, 45, 6309-6312.	3.2	20
61	Quasi-one-dimensional transport in semiconductor microstructures. Physica Scripta, 1992, T45, 200-205.	2.5	4
62	Far-Infrared Transmission of Voltage-Tunable GaAs-(Ga,Al)As Quantum Dots in High Magnetic Fields. Springer Series in Solid-state Sciences, 1992, , 339-343.	0.3	0
63	Thermal Transport in Free-Standing GaAs Wires in a High Magnetic Field. Springer Series in Solid-state Sciences, 1992, , 325-328.	0.3	0
64	Rapid Electron Beam and Optical Furnace Alloying of AuGe/Ni Contacts to GaAs. Physica Status Solidi A, 1991, 125, 255-262.	1.7	1
65	Transmission coefficients and Hall resistance in a small cross-shaped semiconductor junction. Journal of Physics Condensed Matter, 1991, 3, 1961-1965.	1.8	4
66	Aspects of One Dimensional Transport Effects in Gallium Arsenide Heterojunction Structures. NATO ASI Series Series B: Physics, 1991, , 451-467.	0.2	0
67	Differential negative resistance in a one-dimensional mesoscopic system due to single-electron tunnelling. Journal of Physics Condensed Matter, 1990, 2, 2105-2109.	1.8	9
68	One-dimensional ballistic transport of electrons. Semiconductor Science and Technology, 1990, 5, 1185-1188.	2.0	4
69	Quantum conductivity corrections in free-standing and supported n+-GaAs wires. Journal of Physics Condensed Matter, 1990, 2, 1807-1815.	1.8	13
70	Electron heating effects in free-standing single-crystal GaAs fine wires. Journal of Physics Condensed Matter, 1990, 2, 1817-1825.	1.8	22
71	Electron interactions in the two-dimensional electron-gas base of a vertical hot-electron transistor. Physical Review B, 1990, 42, 11415-11418.	3.2	14
72	Transport in a superlattice of 1D ballistic channels. Journal of Physics Condensed Matter, 1990, 2, 3405-3414.	1.8	59

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73	Controllable Scattering, Fabry-Pérot States and Quantum Coupling in Ballistic Devices. Springer Series in Solid-state Sciences, 1990, , 88-98.	0.3	0
74	Empirical relation between gate voltage and electrostatic potential in the one-dimensional electron gas of a split-gate device. Physical Review B, 1989, 39, 6283-6286.	3.2	77
75	Resonant magneto-transport through a lateral quantum box in a semiconductor heterostructure. Journal of Physics Condensed Matter, 1989, 1, 6291-6298.	1.8	50
76	Electronic instabilities in the hot-electron regime of the one-dimensional ballistic resistor. Journal of Physics Condensed Matter, 1989, 1, 6285-6290.	1.8	31
77	Fabry-Perot interferometry with electron waves. Journal of Physics Condensed Matter, 1989, 1, 9035-9044.	1.8	39
78	Observation of Aharonov-Bohm oscillations in a narrow two-dimensional electron gas. Journal of Physics Condensed Matter, 1989, 1, 3369-3373.	1.8	34
79	One-dimensional quantised ballistic resistors in parallel configuration. Journal of Physics Condensed Matter, 1989, 1, 6763-6770.	1.8	63
80	The Growth and Physics of MBE Structures. Physica Scripta, 1989, T29, 141-146.	2.5	0
81	Ballistic Transport in Quasi-One-Dimensional Structures. NATO ASI Series Series B: Physics, 1989, , 115-141.	0.2	0
82	Quantisation of Resistance in One-Dimensional Ballistic Transport. Springer Series in Solid-state Sciences, 1989, , 366-370.	0.3	0
83	One-dimensional transport and the quantisation of the ballistic resistance. Journal of Physics C: Solid State Physics, 1988, 21, L209-L214.	1.5	1,885
84	Fabrication of free-standing single-crystal silicon wires. Applied Physics Letters, 1988, 52, 834-835.	3.3	14
85	Fabrication of submicrometer freestanding single-crystal gallium arsenide and silicon structures for quantum transport studies. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1849.	1.6	25
86	The transition from one- to zero-dimensional ballistic transport. Journal of Physics C: Solid State Physics, 1988, 21, L893-L898.	1.5	102
87	Addition of the one-dimensional quantised ballistic resistance. Journal of Physics C: Solid State Physics, 1988, 21, L887-L891.	1.5	158
88	Diffusion and Activation During Rapid Thermal Annealing of Implanted Boron in Silicon. Materials Research Society Symposia Proceedings, 1985, 52, 65.	0.1	12
89	Electron beam system for rapid isothermal annealing of semiconductor materials and devices. Review of Scientific Instruments, 1985, 56, 1257-1261.	1.3	26